

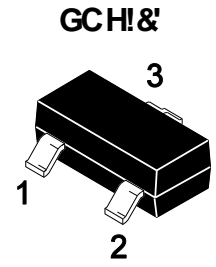


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Silicon Epitaxial Planar Switching Diode

Features

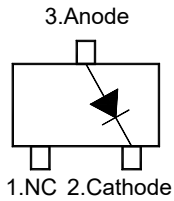
- Fast Switching Speed
- For surface mount applications
- Ideal for automated placement



1.NC 2.Cathode 3.Anode

Marking Code :A6

Pin Configuration



Electrical Characteristics (T_J = 25°C)

| Parameter | Symbol | Value | Unit |
|---|------------------|-------------|------|
| Maximum Repetitive Peak Reverse Voltage | V _{RRM} | 70 | V |
| Reverse Voltage | V _R | 70 | V |
| Continuous forward current | I _F | 100 | mA |
| Peak Forward Surge Current at t = 8.3ms | I _{FSM} | 2 | A |
| Maximum Power Dissipation | P _D | 350 | mW |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature Range | T _{STG} | -65 to +150 | °C |

Electrical Characteristics (T_J = 25°C)

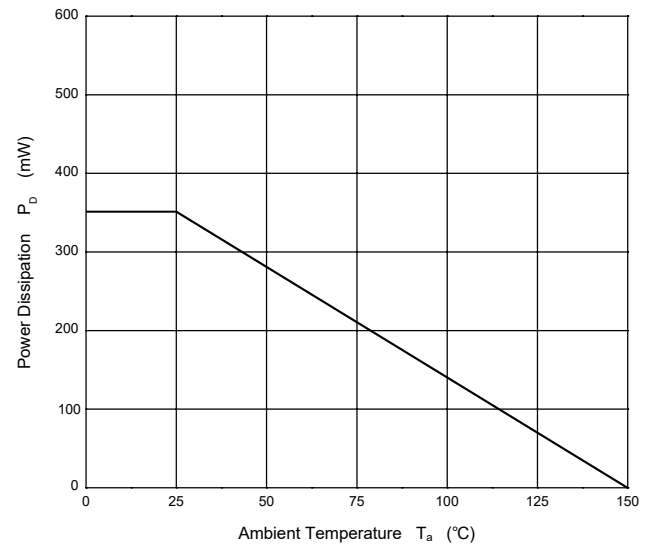
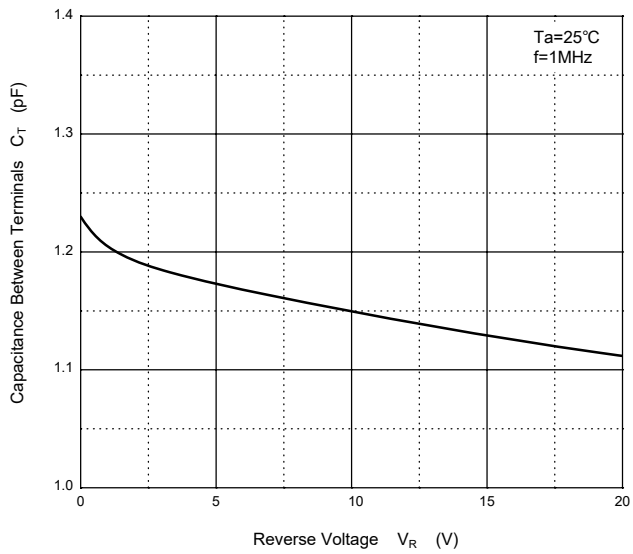
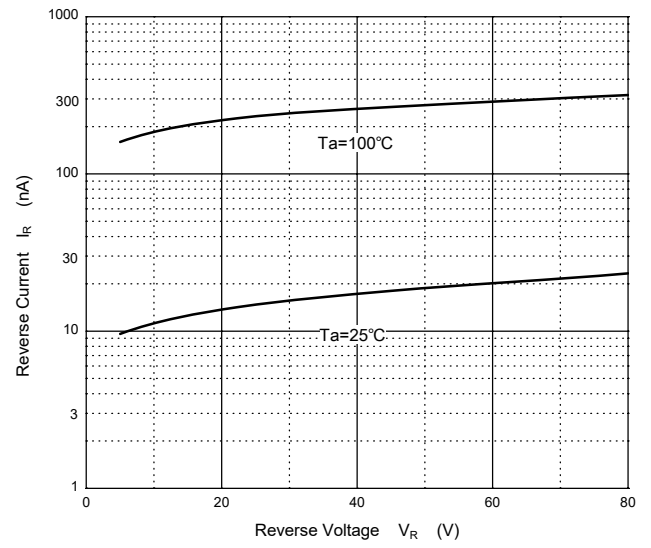
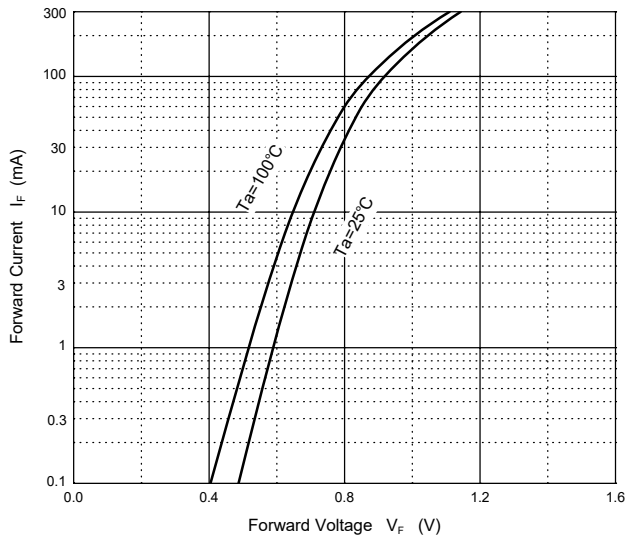
| Parameter | Symbol | Max. | Unit |
|---|-----------------|-----------------------------|------|
| Forward Voltage at I _F = 1 mA at I _F = 10 mA at I _F = 50 mA at I _F = 150 mA | V _F | 0.715 0.855 1 1.25 | V |
| Reverse Current at V _R = 70 V | I _R | 0.03 | μA |
| Typical Junction Capacitance at V _R = 4 V, f = 1 MHz | C _j | 1.5 | pF |
| Maximum Reverse Recovery Time | T _{rr} | 4 | μS |



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Typical Characteristic Curves





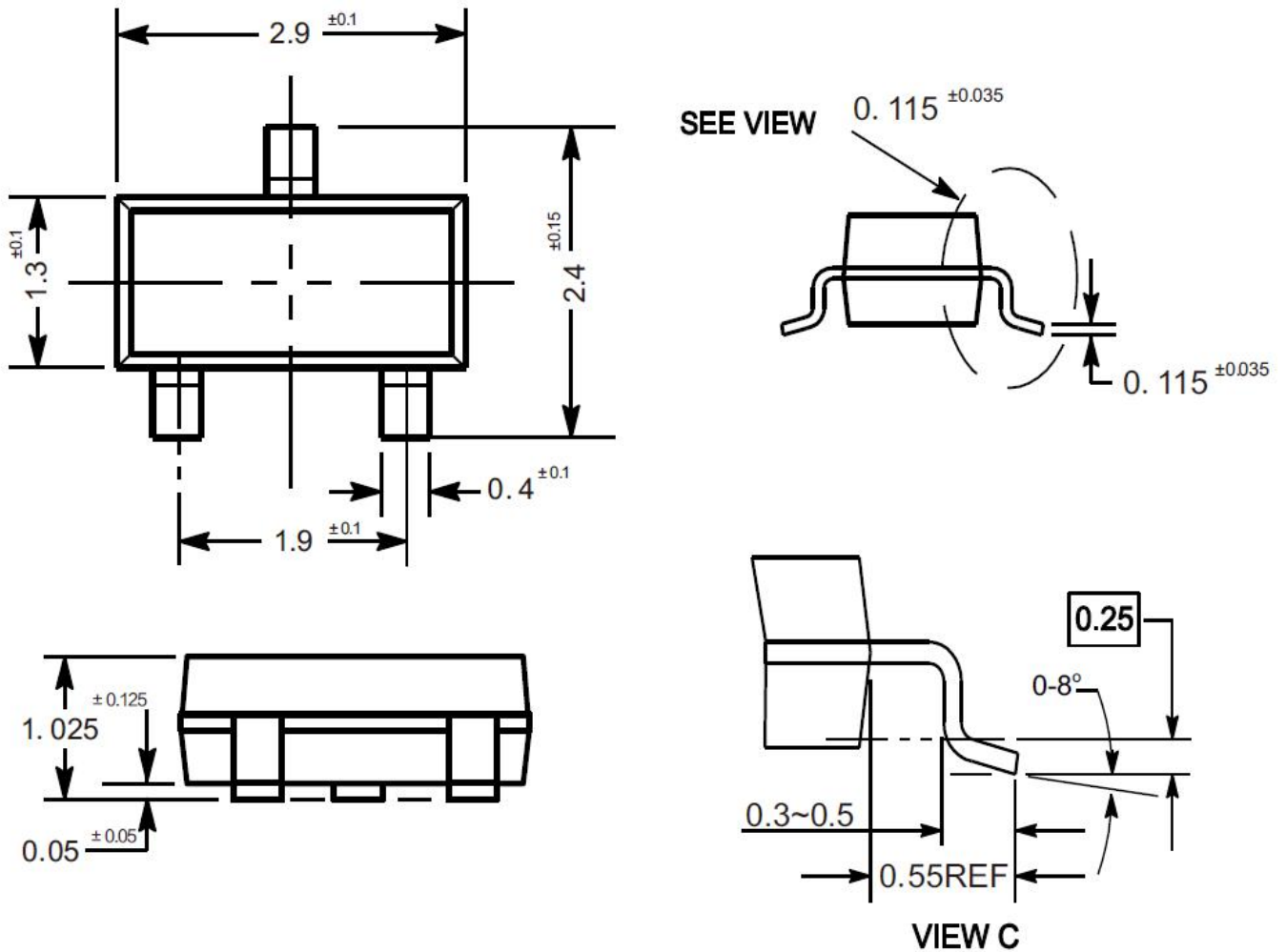
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Silicon Epitaxial Planar Switching Diode

Package Outline

SOT-23

Dimensions in mm



Ordering Information

| Device | Package | Shipping |
|--------|---------|-----------------------|
| BAL99 | SOT-23 | 3,000PCS/Reel&7inches |